## **NPN Silicon Epitaxial Planar Transistor**

for switching and AF amplifier applications.

The transistor is subdivided into six groups, D, E, F, G, H and I, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings (T<sub>a</sub> = 25℃)

|                           | Symbol           | Value       | Unit |
|---------------------------|------------------|-------------|------|
| Collector Base Voltage    | V <sub>CBO</sub> | 50          | V    |
| Collector Emitter Voltage | V <sub>CEO</sub> | 30          | V    |
| Emitter Base Voltage      | V <sub>EBO</sub> | 5           | V    |
| Collector Current         | Ic               | 30          | mA   |
| Power Dissipation         | P <sub>tot</sub> | 400         | mW   |
| Junction Temperature      | T <sub>j</sub>   | 150         | °C   |
| Storage Temperature Range | Ts               | -55 to +150 | °C   |

#### **G S P FORM A IS AVAILABLE**









# Characteristics at T<sub>amb</sub>=25 °C

|  | Symbol           | Min. | Тур. | Max. | Unit |
|--|------------------|------|------|------|------|
| DC Current Gain                              |                  |      |      |      |      |
| at V <sub>CE</sub> =5V, I <sub>C</sub> =1mA  |                  |      |      |      |      |
| Current Gain Group D                         | $h_{FE}$         | 28   | -    | 45   | -    |
| E  | $h_{FE}$         | 39   | -    | 60   | -    |
| F  | h <sub>FE</sub>  | 54   | -    | 80   | -    |
| G  | h <sub>FE</sub>  | 72   | -    | 108  | -    |
| н  | h <sub>FE</sub>  | 97   | -    | 146  | -    |
| I  | h <sub>FE</sub>  | 132  | -    | 198  | -    |
| Collector Base Breakdown Voltage             |                  |      |      |      |      |
| at I <sub>C</sub> =100μA                     | $V_{(BR)CBO}$    | 50   | -    | -    | V    |
| Collector Emitter Breakdown Voltage          |                  |      |      |      |      |
| at I <sub>C</sub> =1mA                       | $V_{(BR)CEO}$    | 30   | -    | -    | V    |
| Emitter Base Breakdown Voltage               |                  |      |      |      |      |
| at I <sub>E</sub> =100μA                     | $V_{(BR)EBO}$    | 5    | -    | -    | V    |
| Collector Cutoff Current                     |                  |      |      |      |      |
| at V <sub>CB</sub> =50V                      | $I_{CBO}$        | -    | -    | 100  | nA   |
| Emitter Cutoff Current                       |                  |      |      |      |      |
| at V <sub>CB</sub> =5V                       | I <sub>EBO</sub> | -    | -    | 100  | nA   |
| Collector Emitter Saturation Voltage         |                  |      |      |      |      |
| at I <sub>C</sub> =10mA, I <sub>B</sub> =1mA | $V_{CE(sat)}$    | -    | 0.08 | 0.3  | V    |
| Base Emitter Voltage                         |                  |      |      |      |      |
| at V <sub>CE</sub> =5V, I <sub>C</sub> =1mA  | $V_{BE(on)}$     | 0.60 | 0.7  | 0.75 | V    |
| Collector Base Capacitance                   |                  |      |      |      |      |
| at V <sub>CB</sub> =10V, f=1MHz              | $C_{CBO}$        | -    | 1.5  | -    | pF   |
| Gain Bandwidth Product                       |                  |      |      |      |      |
| at V <sub>CE</sub> =5V, I <sub>C</sub> =1mA  | $f_T$            | 150  | 370  | -    | MHz  |

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